

CLAIMS

1. A semiconductor polishing composition comprising:
fumed silica, the semiconductor polishing composition
being an aqueous dispersion solution of fumed silica,
wherein the number of particles of fumed silica having
a particle diameter of 0.5 μm or more is 600,000 pieces/ml or
less and the number of particles of fumed silica having a particle
diameter of 1 μm or more is 6000 pieces/ml or less.
2. The semiconductor polishing composition of claim 1,
wherein the semiconductor polishing composition has the number
of fumed silica particles that have a particle diameter of 0.5
 μm or more in a range of 10,000 to 600,000 pieces/ml.
3. The semiconductor polishing composition of claim 1 or
2, wherein the semiconductor polishing composition has the
number of fumed silica particles that have a particle diameter
of 1 μm or more in a range of 500 to 6000 pieces/ml.
4. The semiconductor polishing composition of any one of
claims 1 to 3, wherein a content of the fumed silica is in a
range of 10 to 30% by weight based on a total amount of the
composition.
5. The semiconductor polishing composition of any one of

claims 1 to 4, wherein the aqueous dispersion solution of fumed silica is prepared by adding an acidic fumed silica dispersion solution to an alkali aqueous solution.

6. The semiconductor polishing composition of claim 5, wherein a pH of the alkali aqueous solution is in a range of 12 to 14.